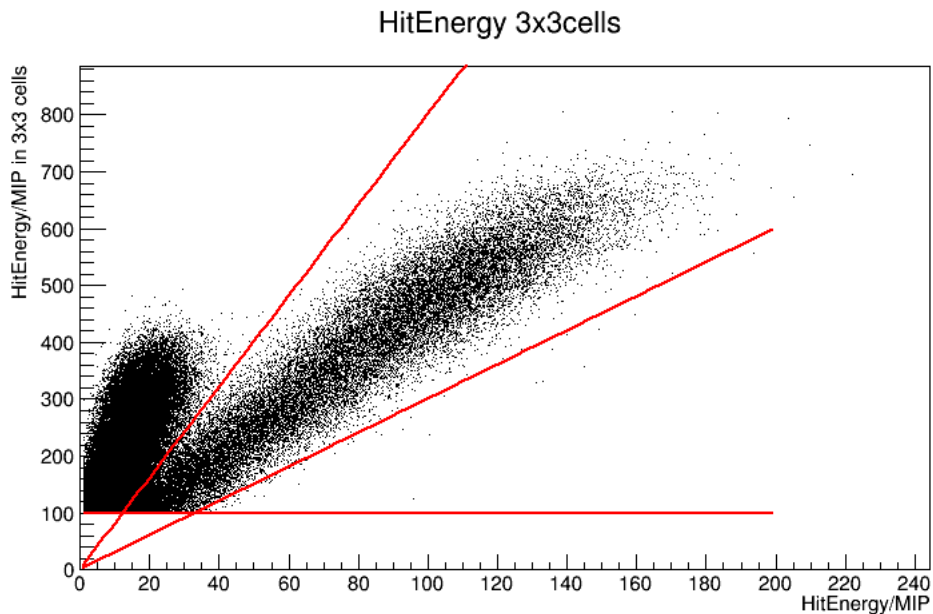
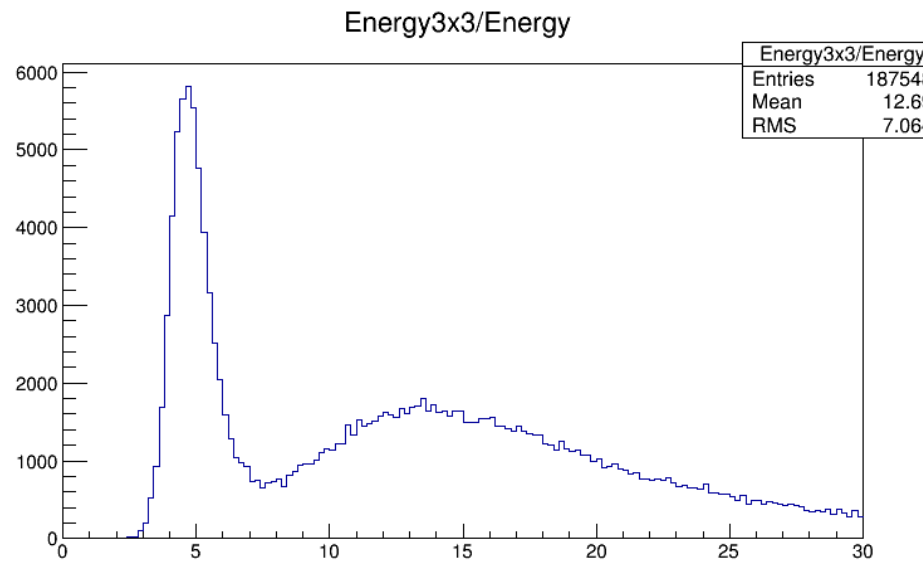


刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布

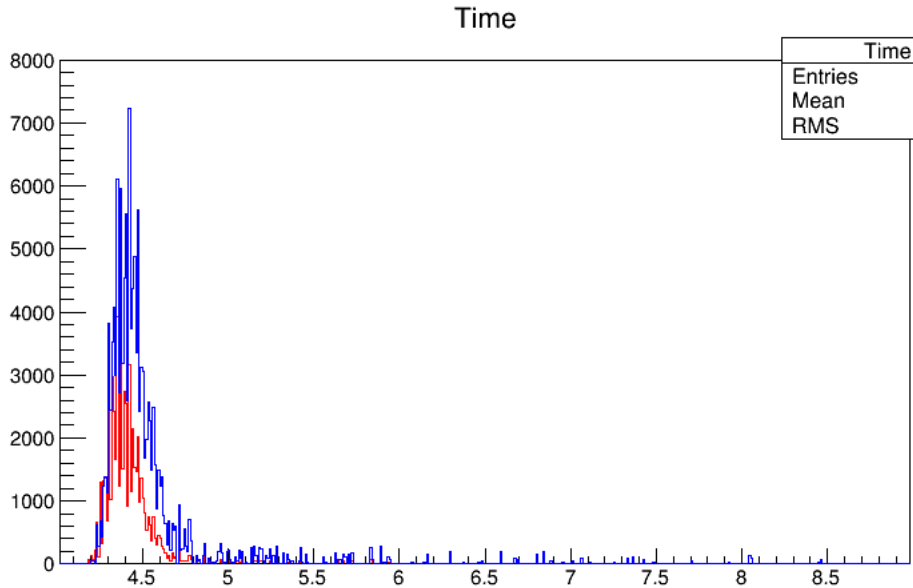


Cell Size 5x5mm

100GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm

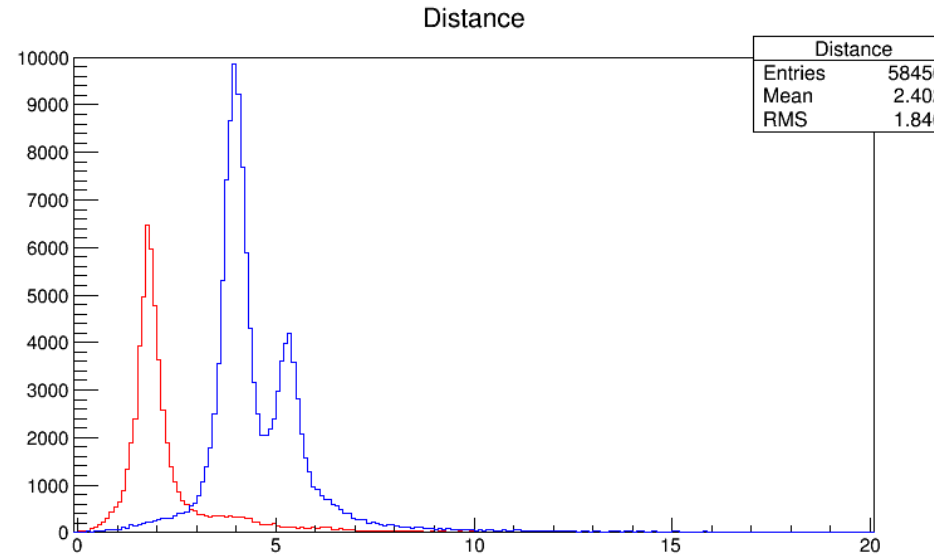
刻度研究

——击中点能量与其周围能量的关系



Hit Energy 3x3 neighbor/HitEnergy with Time

蓝色比值大于8，红色比值3~8

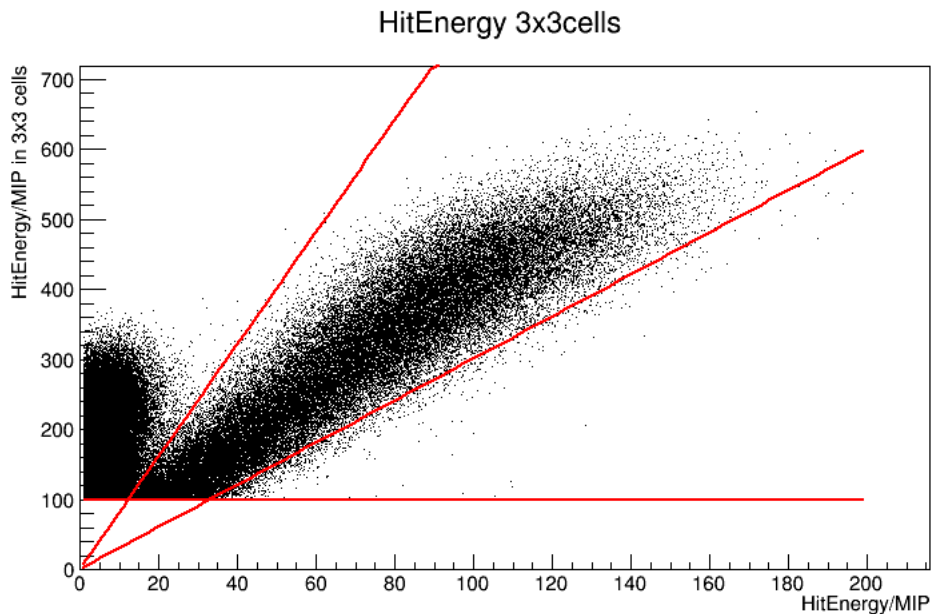


Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

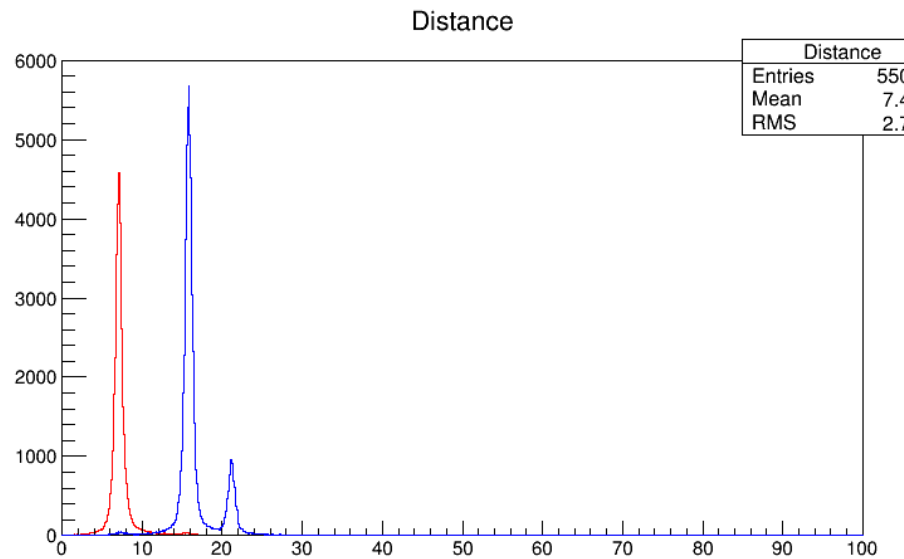
100GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 2.5x2.5mm

刻度研究

——击中点能量与其周围能量的关系



Hit Energy/MIP 分布



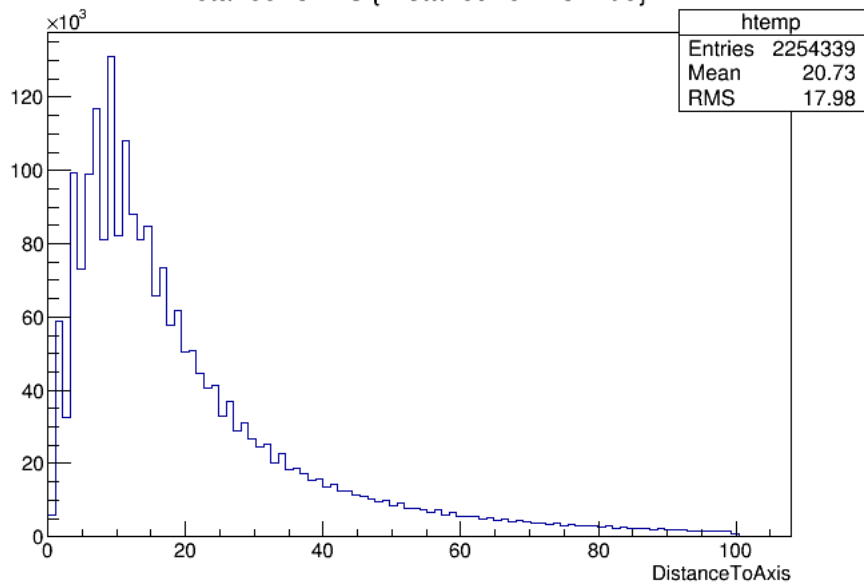
Hit Energy 3x3 neighbor/HitEnergy with Distance from Hit to Axis

蓝色比值大于8，红色比值3~8

50GeV photon, 大于1MIP, 灵敏体积厚度2mm, Cell Size 10x10mm

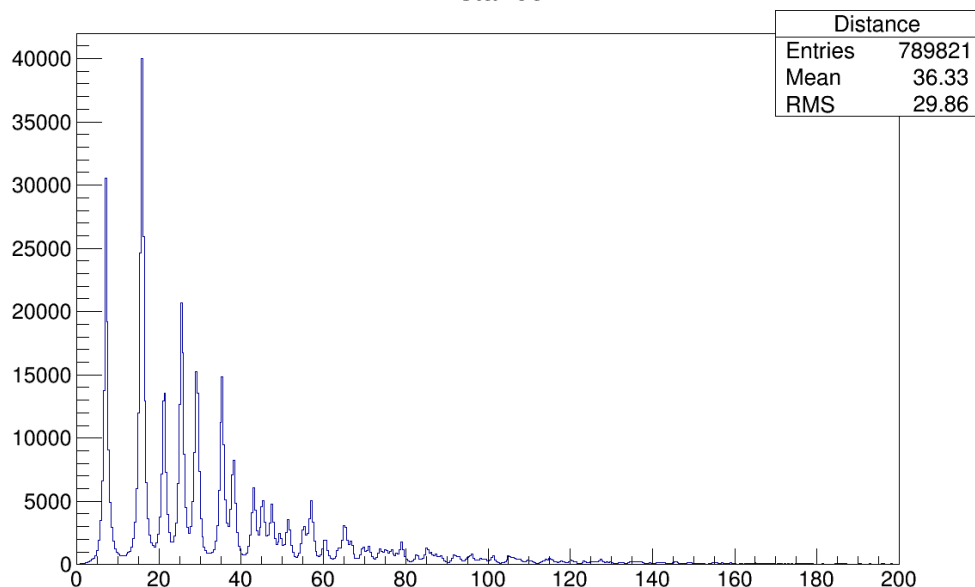
到簇射轴距离分布

DistanceToAxis {DistanceToAxis<100}



50GeVphoton
Cell Size 2.5x2.5mm

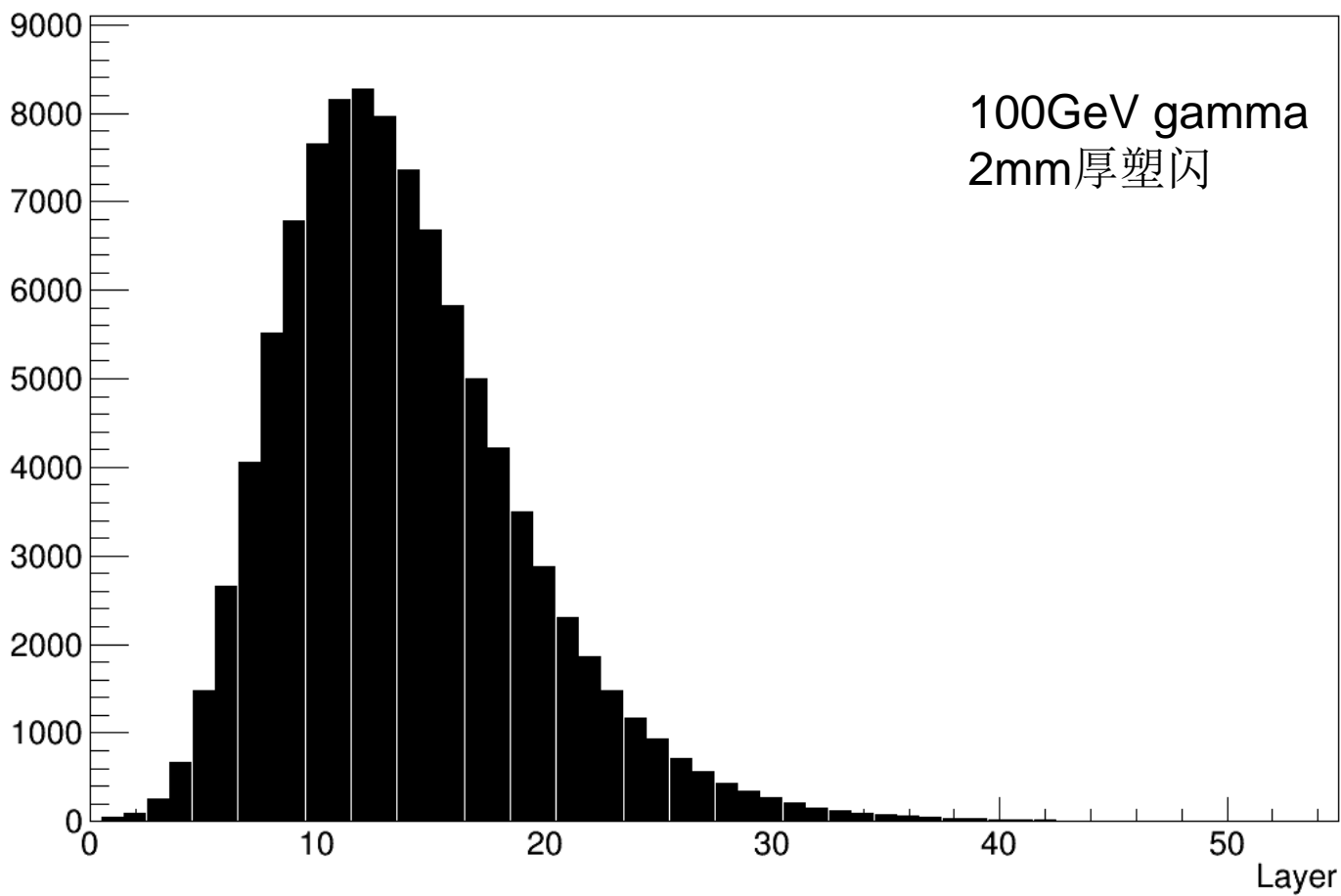
Distance



50GeVphoton
Cell Size 10x10mm

层数对能量泄露影响

Energy in layer



单层结构：2mm塑闪+2mmPCB+3mmW

入射粒子为gamma

